

IN THE SPECIFICATION

Please replace the paragraph starting at page 38, line 27 and ending at page 39, line 19 with the following substitute paragraph. A version of this paragraph, marked to show the changes made thereto, is appended.

A1  
--FIG. 33 is a schematic sectional showing an example of such a unit cell, in which a photodiode, a transfer means, and a reset means are shown. Reference numeral 81 denotes a p-type well, reference numeral 82 denotes an oxide film as an element-separating region, reference numeral 83 denotes a cathode of a photodiode, reference numerals 84 and 85 denote respectively a drain and a source of an n-channel MOS transistor as a reset means, and the drain 84 is connected to the input terminal of the amplifying means and the source 85 is connected to the power line for resetting. Reference numerals 86 and 87 denote gate electrodes. Although not shown, n-channel MOS as an amplifying means and a selecting means are likewise built in the p-type well 81. Thus, each element configuring a unit cell comprises the same conductivity type element with electrons being used as transmission carriers. Reference numeral 88 denotes a p-type layer. With the conductivity type being made opposite in FIG. 33, elements using holes as transmission carriers can be used for configuration.--

IN THE CLAIMS

Please amend Claims 1-13 as follows. A version of those claims, marked to show the changes made thereto, is appended: